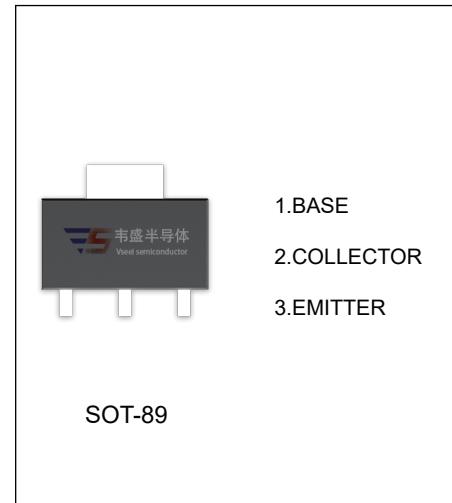


2SC4115 TRANSISTOR (NPN)

FEATURES

- Low $V_{CE(sat)}$. $V_{CE(sat)} = 0.2V$ (Typ.)($I_C / I_B = 2A / 0.1A$)
- Excellent current gain characteristics.
- Complements to 2SA1585



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	6	V
I_c	Collector Current -Continuous	3	A
P_c	Collector Power Dissipation	500	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C= 50\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}= 5\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{V}, I_C= 0.1\text{A}$	120		560	
Collector-emitter saturation voltage*	$V_{CE(sat)}$	$I_C= 2\text{A}, I_B=0.1\text{A}$			0.5	V
Transition frequency	f_T	$V_{CE}=2\text{V}, I_C=0.5\text{ A}$ $F=100\text{MHz}$	200	290		MHz

*pulse test

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560
marking	4115Q	4115R	4115S